

STFW3N150, STH3N150-2, STP3N150, STW3N150

N-channel 1500 V, 2.5 A, 6 Ω typ., PowerMESH™ Power MOSFETs
in TO-3PF, H²PAK-2, TO-220 and TO247 packages

Datasheet - production data

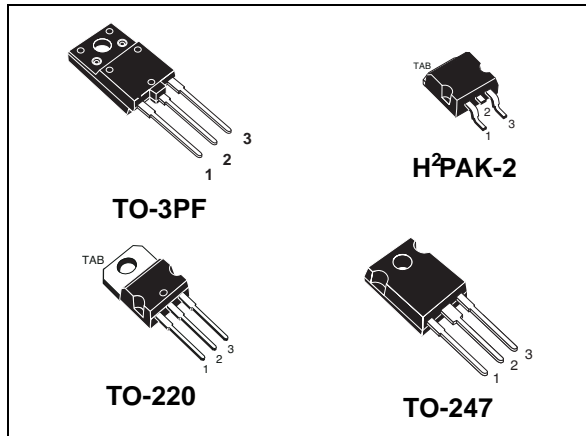
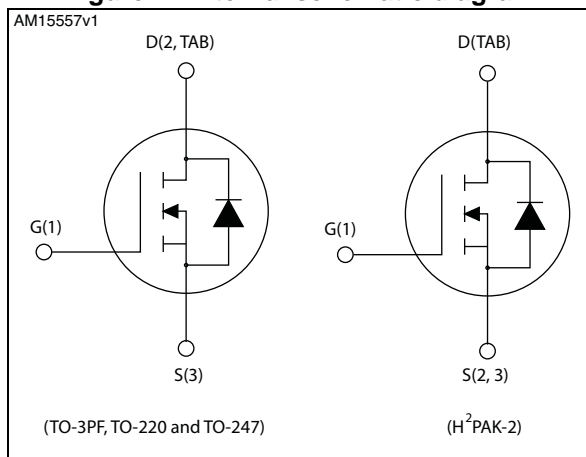


Figure 1. Internal schematic diagram



Features

Order codes	V _{DS}	R _{DS(on)} max.	I _D	P _{TOT}
STFW3N150	1500 V	9 Ω	2.5 A	63 W
STH3N150-2				140 W
STP3N150				
STW3N150				

- 100% avalanche tested
- Intrinsic capacitances and Q_g minimized
- High speed switching
- Fully isolated TO-3PF plastic package, creepage distance path is 5.4 mm (typ.)

Applications

- Switching applications

Description

These Power MOSFETs are designed using the company's consolidated strip layout-based MESH OVERLAY™ process. The result is a product that matches or improves on the performance of comparable standard parts from other manufacturers.

Table 1. Device summary

Order codes	Marking	Packages	Packaging
STFW3N150	3N150	TO-3PF	Tube
STH3N150-2		H ² PAK-2	Tape and reel
STP3N150		TO-220	Tube
STW3N150		TO-247	

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1 Electrical ratings

Table 2. Absolute maximum ratings

Symbol	Parameter	Value		Unit
		TO-3PF	H ² PAK-2, TO-220, TO-247	
V _{DS}	Drain-source voltage	1500		V
V _{GS}	Gate-source voltage	± 30		V
I _D	Drain current (continuous) at T _C = 25 °C	2.5 ⁽¹⁾	2.5	A
I _D	Drain current (continuous) at T _C = 100 °C	1.6 ⁽¹⁾	1.6	A
I _{DM} ⁽¹⁾	Drain current (pulsed)	10 ⁽¹⁾	10	A
P _{TOT}	Total dissipation at T _C = 25 °C	63	140	W
V _{ISO}	Insulation withstand voltage (RMS) from all three leads to external heat sink (t=1 s; T _C =25 °C)	3500		V
	Derating factor	0.5	1.12	W/°C
T _{stg}	Storage temperature	-50 to 150		°C
T _j	Max. operating junction temperature	150		°C

1. Pulse width limited by safe operating area

Table 3. Thermal data

Symbol	Parameter	TO-3PF	H ² PAK-2	TO-220	TO-247	Unit
R _{thj-case}	Thermal resistance junction-case max	2	0.89			°C/W
R _{thj-amb}	Thermal resistance junction-ambient max	50		62.5	50	°C/W
R _{thj-pcb}	Thermal resistance junction-pcb max		35 ⁽¹⁾			°C/W

1. When mounted on 1 inch² FR-4 board, 2 oz Cu

Table 4. Avalanche characteristics

Symbol	Parameter	Max value	Unit
I _{AR}	Avalanche current, repetitive or not-repetitive (pulse width limited by T _j max)	2.5	A
E _{AS}	Single pulse avalanche energy (starting T _j = 25 °C, I _D = I _{AR} , V _{DD} = 50 V)	450	mJ

2 Electrical characteristics

($T_{\text{case}} = 25\text{ °C}$ unless otherwise specified)

Table 5. On /off states

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	$I_D = 1\text{ mA}$, $V_{GS} = 0$	1500			V
I_{DSS}	Zero gate voltage drain current ($V_{GS} = 0$)	$V_{DS} = 1500\text{ V}$			10	μA
		$V_{DS} = 1500\text{ V}$, $T_C = 125\text{ °C}$			500	μA
I_{GSS}	Gate-body leakage current ($V_{DS} = 0$)	$V_{GS} = \pm 30\text{ V}$			± 100	nA
$V_{GS(th)}$	Gate threshold voltage	$V_{DS} = V_{GS}$, $I_D = 250\text{ }\mu\text{A}$	3	4	5	V
$R_{DS(on)}$	Static drain-source on-resistance	$V_{GS} = 10\text{ V}$, $I_D = 1.3\text{ A}$		6	9	Ω

Table 6. Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$g_{fs}^{(1)}$	Forward transconductance	$V_{DS} = 30\text{ V}$, $I_D = 1.3\text{ A}$	-	2.6	-	S
C_{iss}	Input capacitance	$V_{DS} = 25\text{ V}$, $f = 1\text{ MHz}$, $V_{GS} = 0$	-	939	-	pF
			-		-	pF
			-		-	pF
C_{oss}	Output capacitance	$V_{DS} = 25\text{ V}$, $f = 1\text{ MHz}$, $V_{GS} = 0$	-	102	-	pF
C_{rss}	Reverse transfer capacitance		-	13.2	-	pF
$C_{oss\text{ eq.}}^{(2)}$	Equivalent output capacitance	$V_{DS} = 0$ to 1200 V , $V_{GS} = 0$	-	100	-	pF
R_g	Gate input resistance	$f = 1\text{ MHz}$, gate DC Bias = 0, test signal level = 20 mV, $I_D = 0$	-	4	-	Ω
Q_g	Total gate charge	$V_{DD} = 1200\text{ V}$, $I_D = 2.5\text{ A}$,	-	29.3	-	nC
Q_{gs}	Gate-source charge	$V_{GS} = 10\text{ V}$	-	4.6	-	nC
Q_{gd}	Gate-drain charge	(Figure 19)	-	17	-	nC

1. Pulsed: pulse duration = 300 μs , duty cycle 1.5%

2. $C_{oss\text{ eq.}}$ is defined as a constant equivalent capacitance giving the same charging time as C_{oss} when V_{DS} increases from 0 to 80% V_{DSS}

Table 7. Switching times

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on delay time	$V_{DD} = 750 \text{ V}$, $I_D = 1.25 \text{ A}$, $R_G = 4.7 \text{ } \Omega$, $V_{GS} = 10 \text{ V}$ (Figure 18)	-	24	-	ns
t_r	Rise time		-	47	-	ns
$t_{d(off)}$	Turn-off-delay time		-	45	-	ns
t_f	Fall time		-	61	-	ns

Table 8. Source drain diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
I_{SD}	Source-drain current		-		2.5	A
$I_{SDM}^{(1)}$	Source-drain current (pulsed)		-		10	A
$V_{SD}^{(2)}$	Forward on voltage	$I_{SD} = 2.5 \text{ A}$, $V_{GS} = 0$	-		1.6	V
t_{rr}	Reverse recovery time	$I_{SD} = 2.5 \text{ A}$, $di/dt = 100 \text{ A}/\mu\text{s}$ $V_{DD} = 60 \text{ V}$ (Figure 20)	-	410		ns
Q_{rr}	Reverse recovery charge		-	2.4		μC
I_{RRM}	Reverse recovery current		-	11.7		A
t_{rr}	Reverse recovery time	$I_{SD} = 2.5 \text{ A}$, $di/dt = 100 \text{ A}/\mu\text{s}$ $V_{DD} = 60 \text{ V}$, $T_j = 150 \text{ }^\circ\text{C}$ (Figure 20)	-	540		ns
Q_{rr}	Reverse recovery charge		-	3.3		μC
I_{RRM}	Reverse recovery current		-	12.3		A

1. Pulse width limited by safe operating area
2. Pulsed: pulse duration = 300 μs , duty cycle 1.5%

2.1 Electrical characteristics (curves)

Figure 2. Safe operating area for TO-3PF

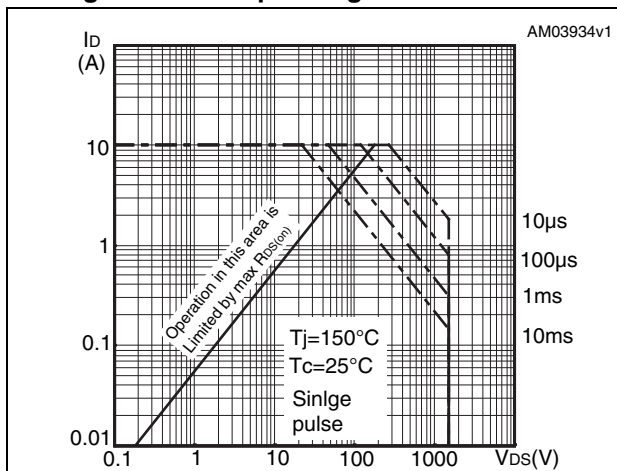


Figure 3. Thermal impedance for TO-3PF

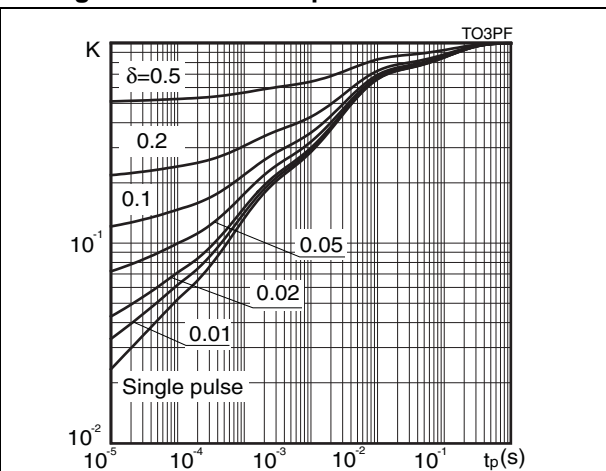


Figure 4. Safe operating area for H²PAK-2 and TO-220

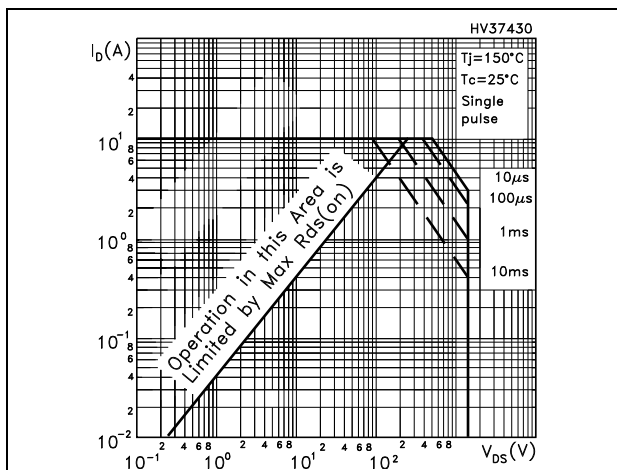


Figure 5. Thermal impedance for H²PAK-2 and TO-220

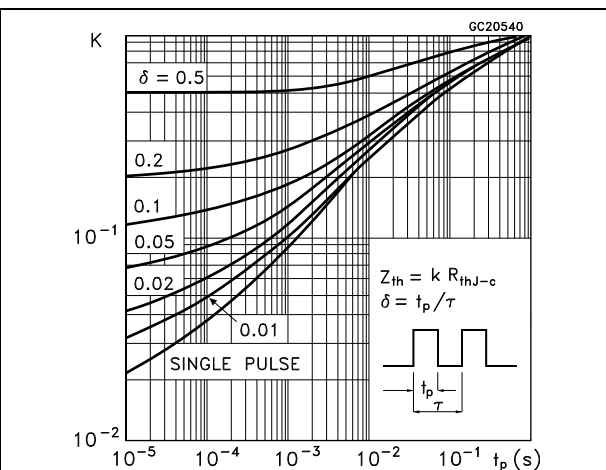


Figure 6. Safe operating area for TO-247

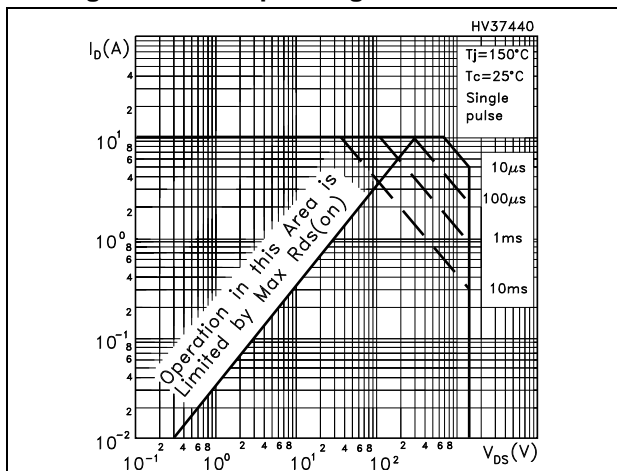


Figure 7. Thermal impedance for TO-247

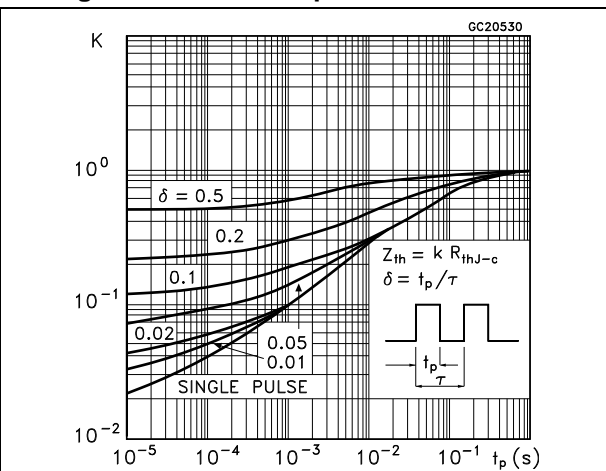


Figure 8. Output characteristics

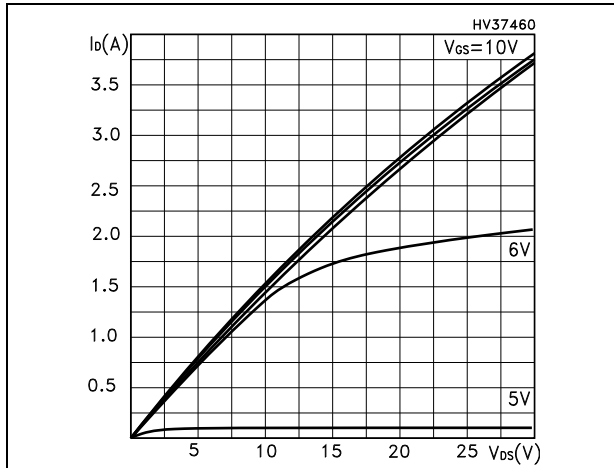


Figure 9. Transfer characteristics

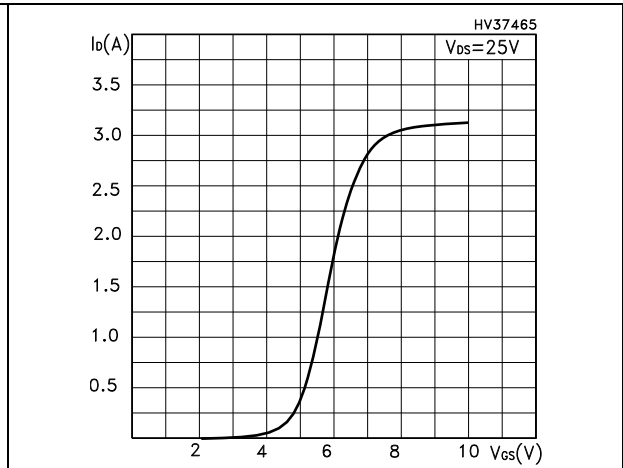


Figure 10. Normalized BV_{DSS} vs. temperature

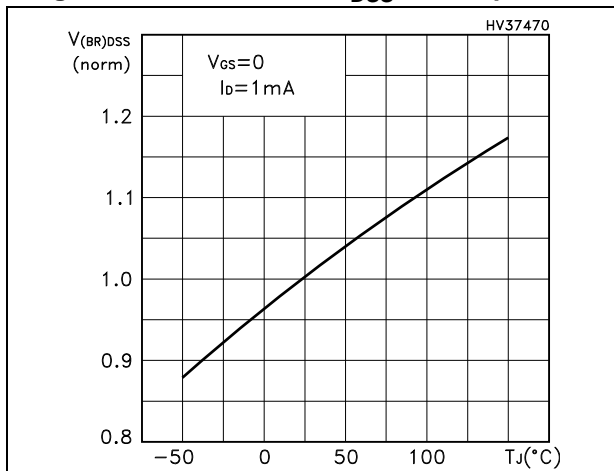


Figure 11. Static drain-source on-resistance

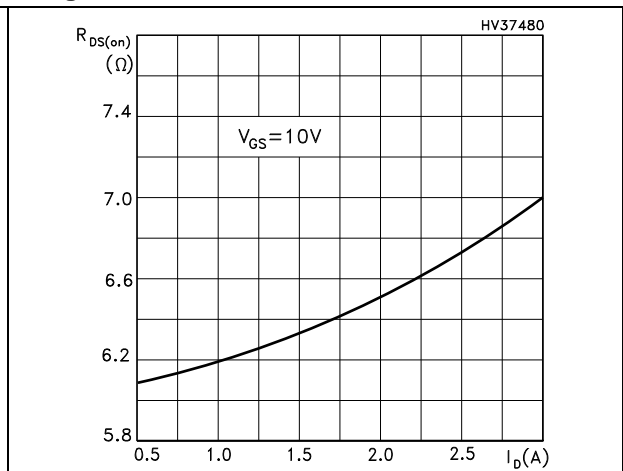


Figure 12. Gate charge vs. gate-source voltage

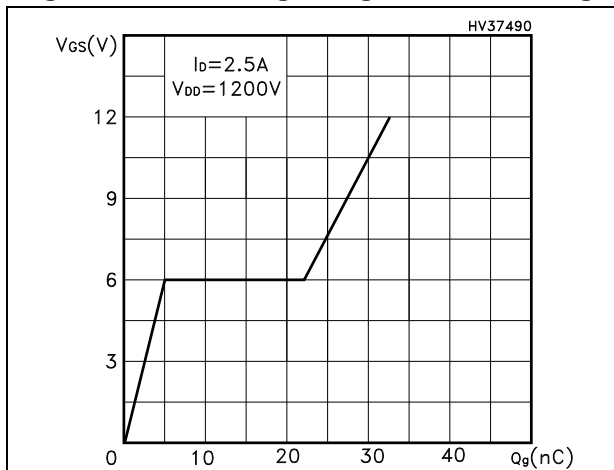


Figure 13. Capacitance variations

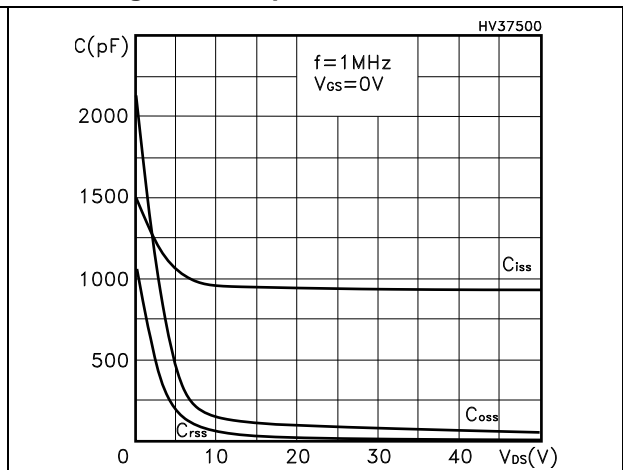


Figure 14. Normalized gate threshold voltage vs. temperature

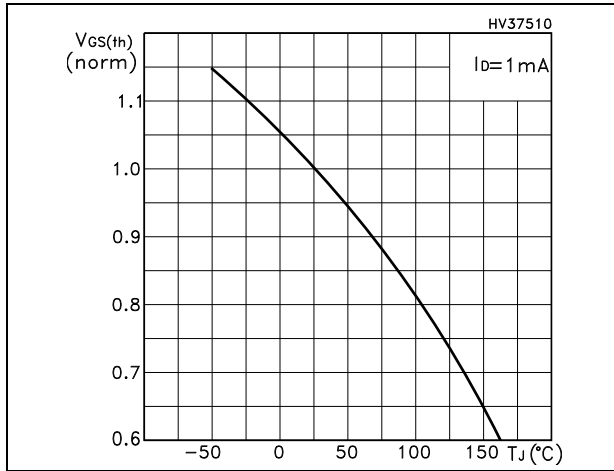


Figure 15. Normalized on resistance vs. temperature

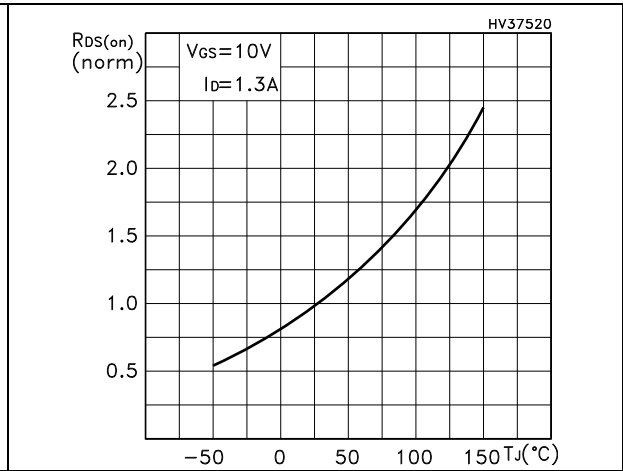


Figure 16. Source-drain diode forward characteristics

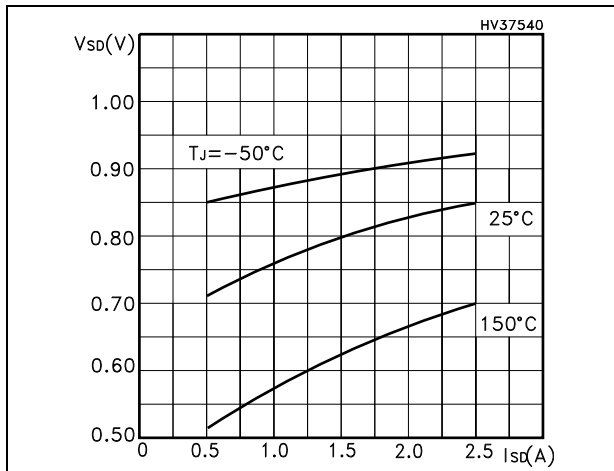
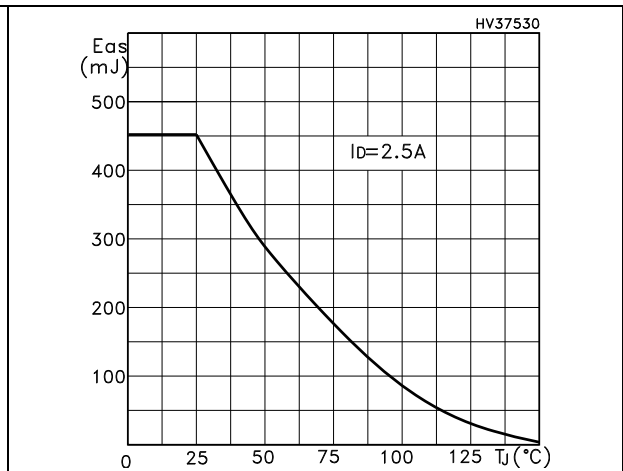
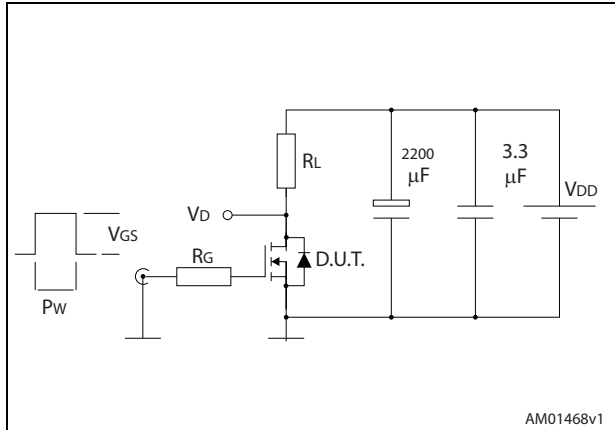


Figure 17. Maximum avalanche energy vs TJ



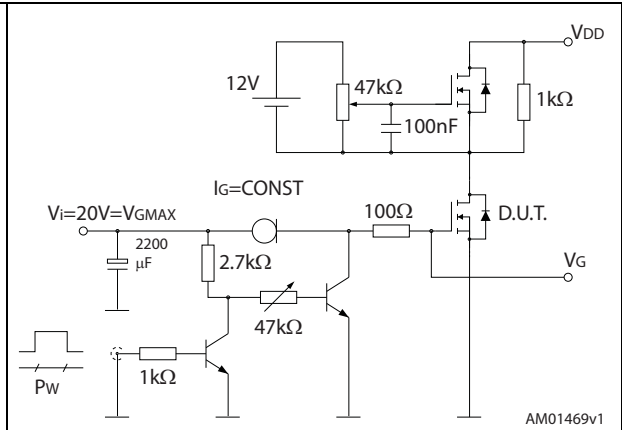
3 Test circuits

Figure 18. Switching times test circuit for resistive load



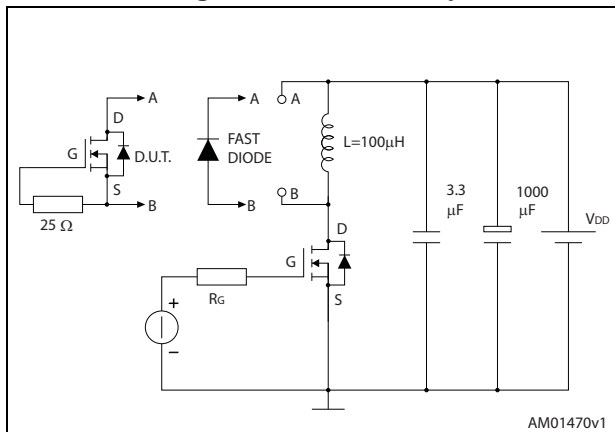
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Figure 19. Gate charge test circuit



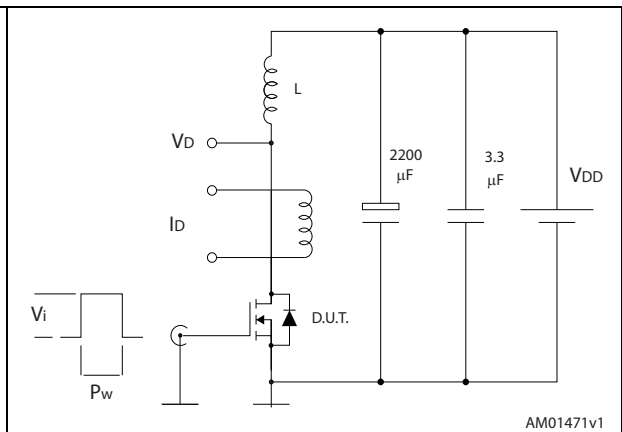
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Figure 20. Test circuit for inductive load switching and diode recovery times



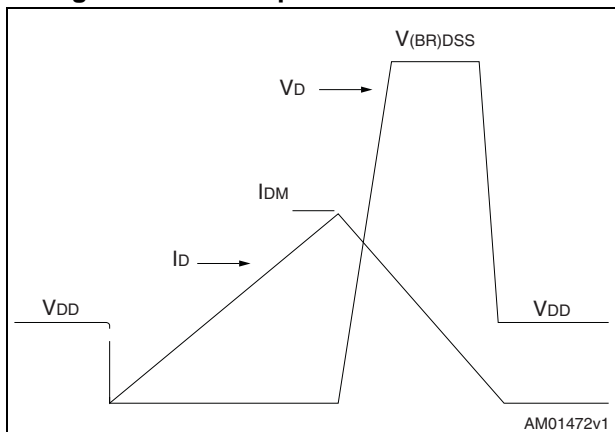
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Figure 21. Unclamped inductive load test circuit



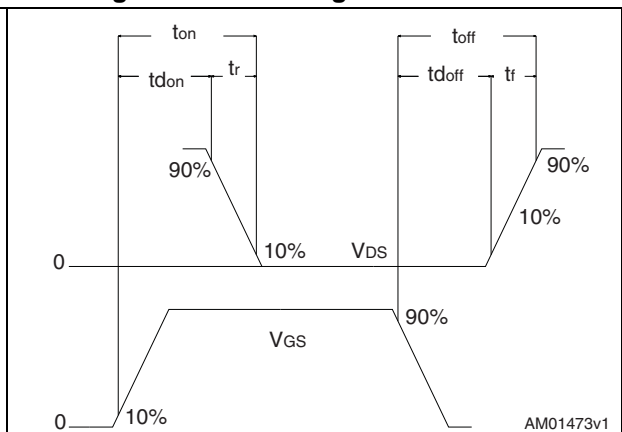
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Figure 22. Unclamped inductive waveform



AM01472v1

Figure 23. Switching time waveform

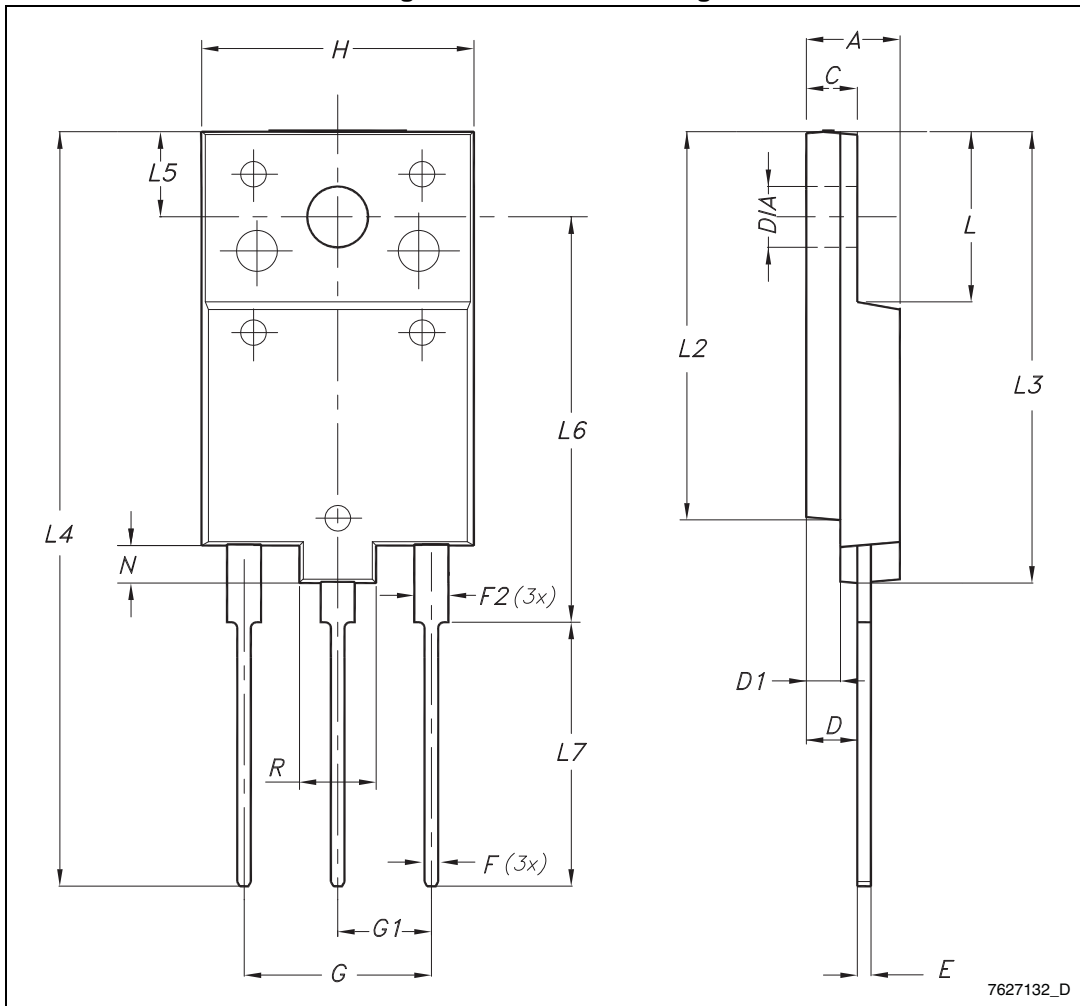


AM01473v1

4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK[®] packages, depending on their level of environmental compliance. ECOPACK[®] specifications, grade definitions and product status are available at: www.st.com. ECOPACK[®] is an ST trademark.

Figure 24. TO-3PF drawing



7627132_D

Table 9. TO-3PF mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	5.30		5.70
C	2.80		3.20
D	3.10		3.50
D1	1.80		2.20
E	0.80		1.10
F	0.65		0.95
F2	1.80		2.20
G	10.30		11.50
G1		5.45	
H	15.30		15.70
L	9.80	10	10.20
L2	22.80		23.20
L3	26.30		26.70
L4	43.20		44.40
L5	4.30		4.70
L6	24.30		24.70
L7	14.60		15
N	1.80		2.20
R	3.80		4.20
Dia	3.40		3.80

Figure 25. H²PAK-2 drawing

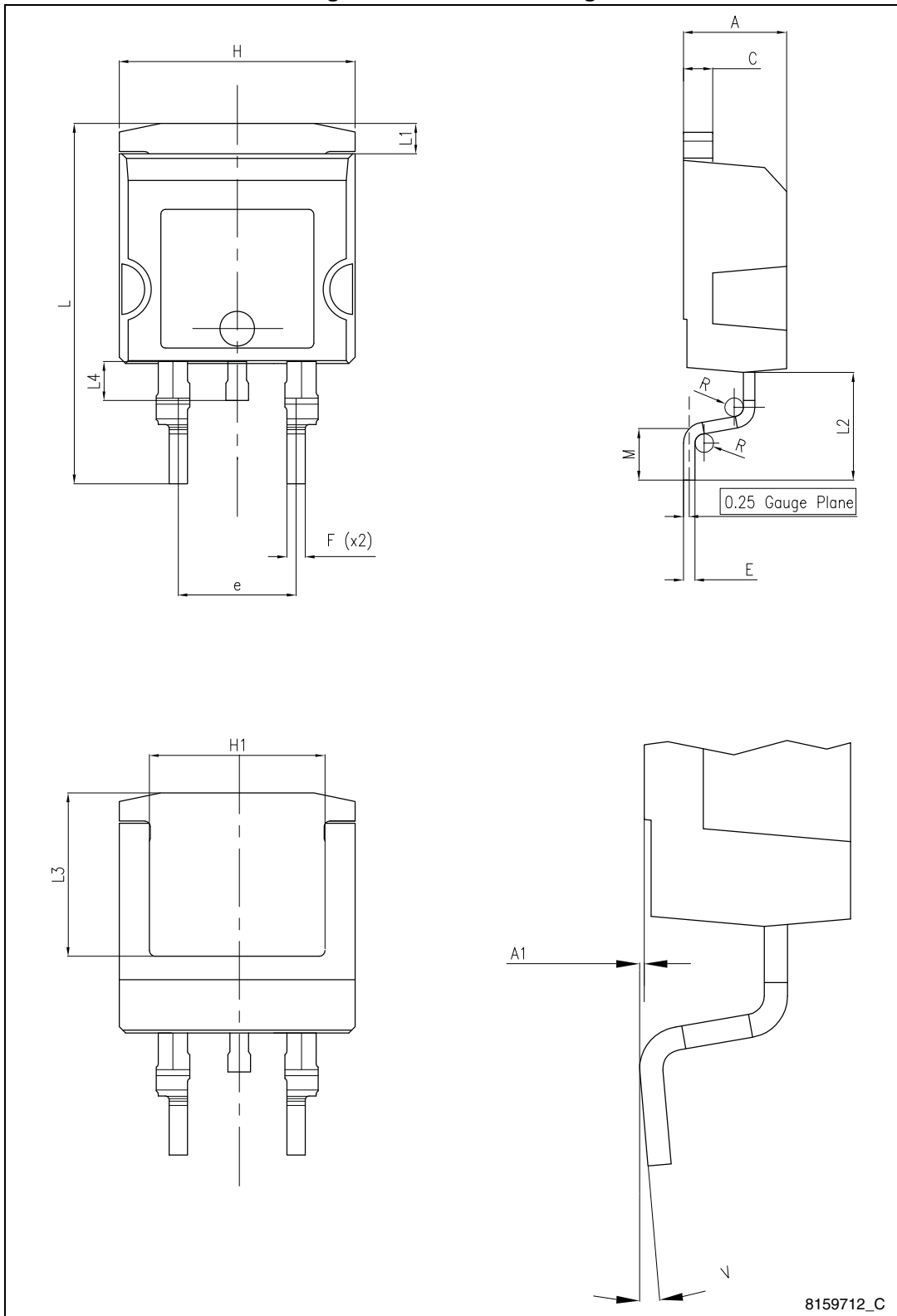


Table 10. H²PAK-2 mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	4.30		4.80
A1	0.03		0.20
C	1.17		1.37
e	4.98		5.18
E	0.50		0.90
F	0.78		0.85
H	10.00		10.40
H1	7.40		7.80
L	15.30		15.80
L1	1.27		1.40
L2	4.93		5.23
L3	6.85		7.25
L4	1.5		1.7
M	2.6		2.9
R	0.20		0.60
V	0°		8°

Figure 26. H²PAK-2 recommended footprint (dimensions are in mm)

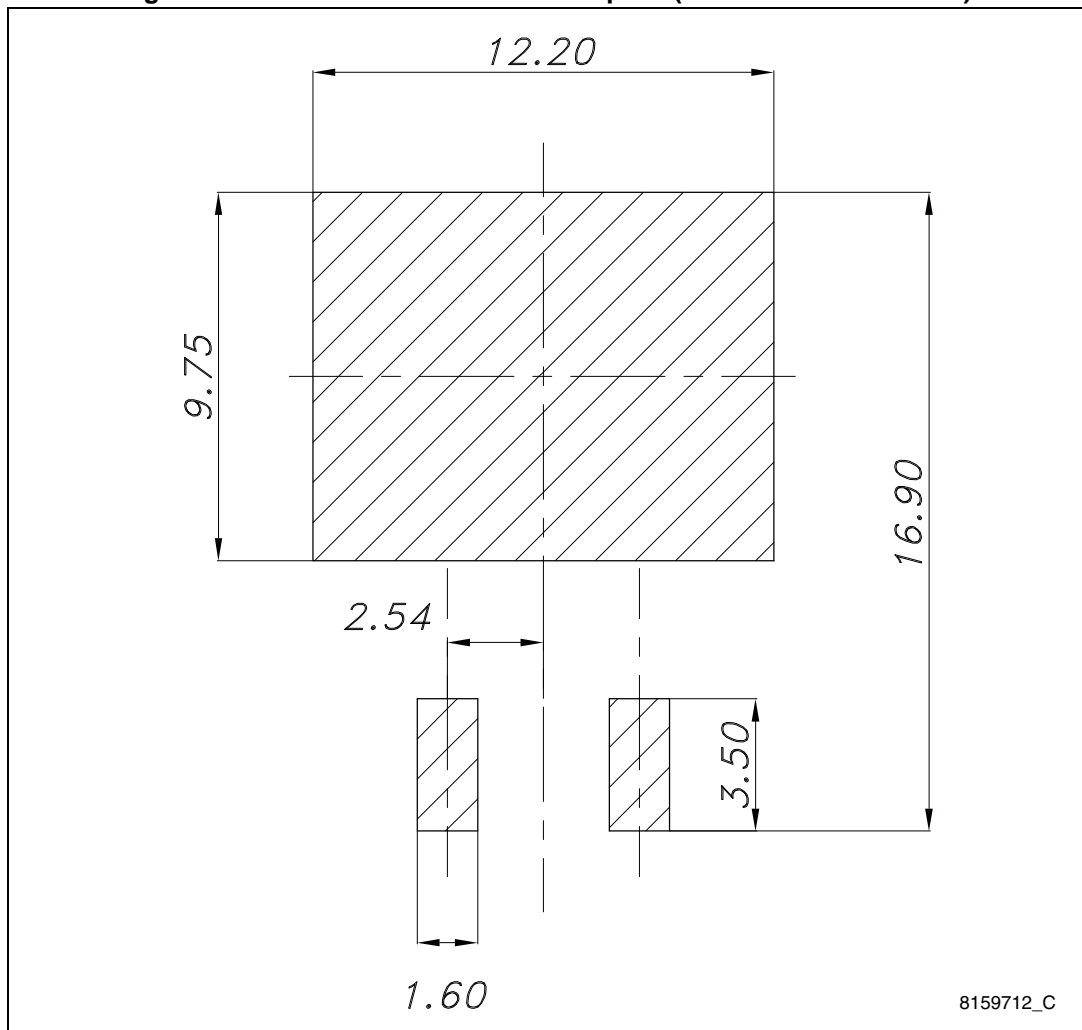


Figure 27. TO-220 type A drawing

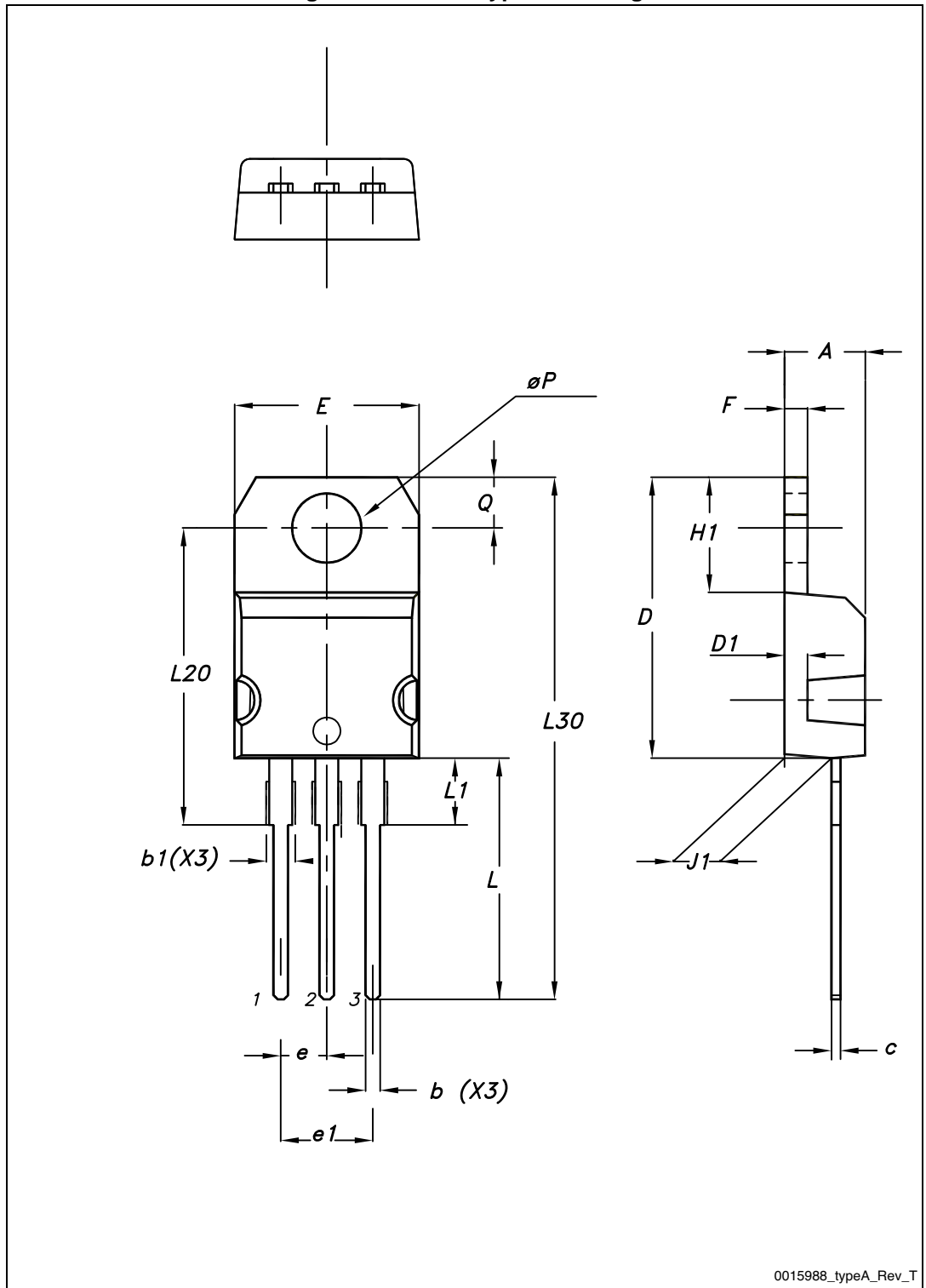


Table 11. TO-220 type A mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	4.40		4.60
b	0.61		0.88
b1	1.14		1.70
c	0.48		0.70
D	15.25		15.75
D1		1.27	
E	10		10.40
e	2.40		2.70
e1	4.95		5.15
F	1.23		1.32
H1	6.20		6.60
J1	2.40		2.72
L	13		14
L1	3.50		3.93
L20		16.40	
L30		28.90	
ØP	3.75		3.85
Q	2.65		2.95

Figure 28. TO-247 drawing

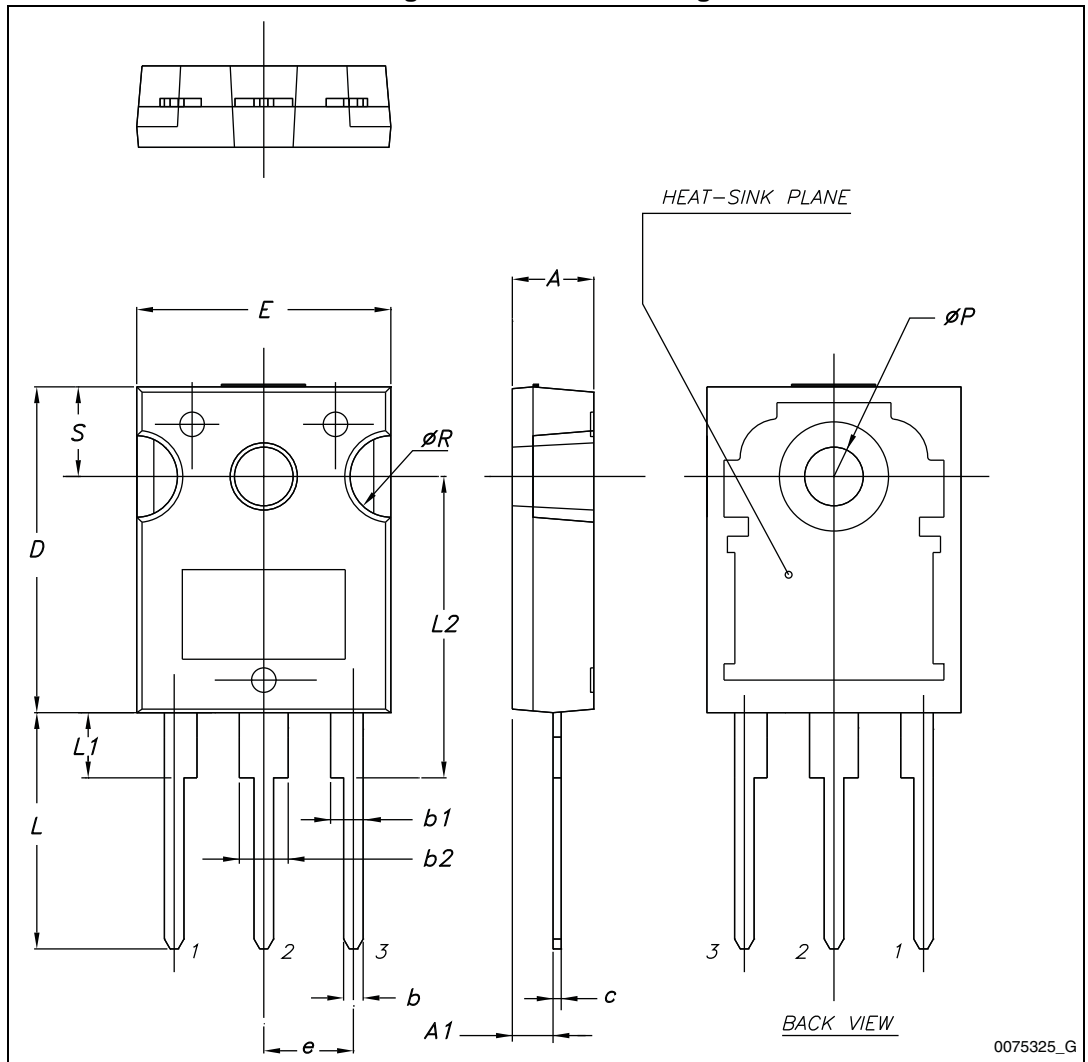


Table 12. TO-247 mechanical data

Dim.	mm.		
	Min.	Typ.	Max.
A	4.85		5.15
A1	2.20		2.60
b	1.0		1.40
b1	2.0		2.40
b2	3.0		3.40
c	0.40		0.80
D	19.85		20.15
E	15.45		15.75
e	5.30	5.45	5.60
L	14.20		14.80
L1	3.70		4.30
L2		18.50	
ØP	3.55		3.65
ØR	4.50		5.50
S	5.30	5.50	5.70

5 Packaging mechanical data

Figure 29. Tape

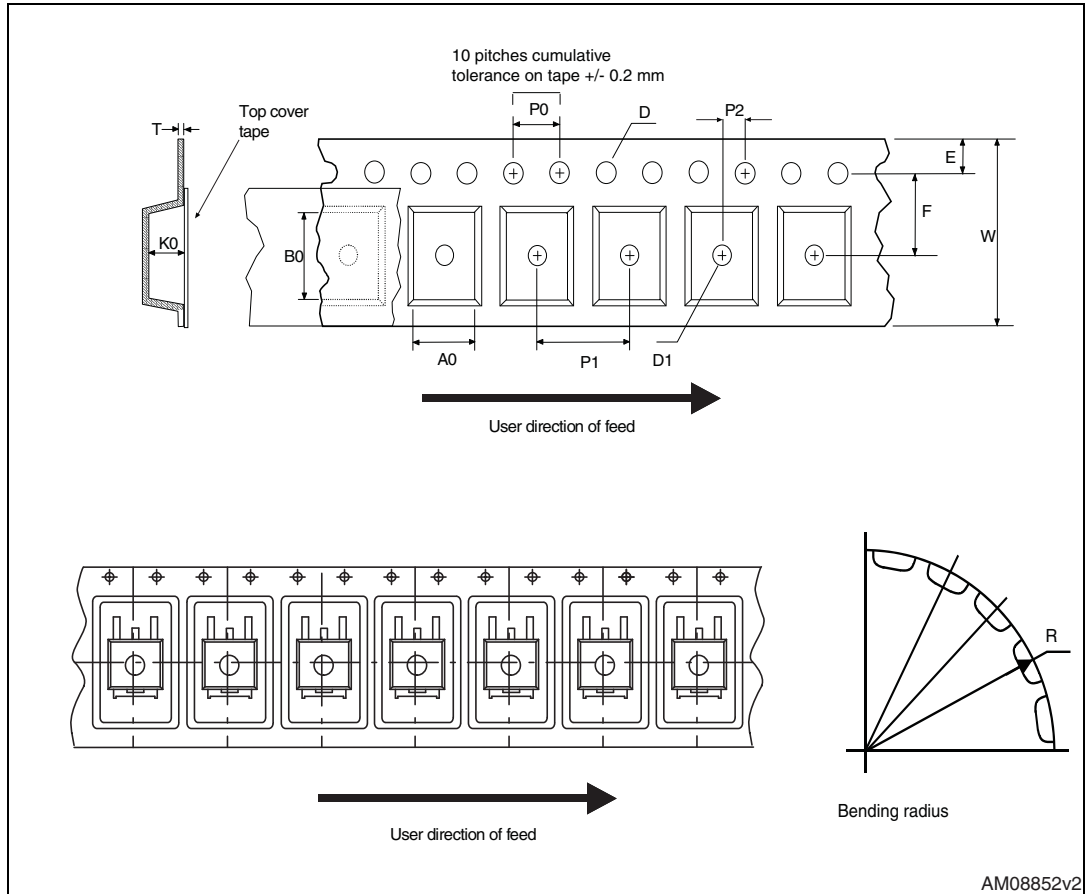


Figure 30. Reel

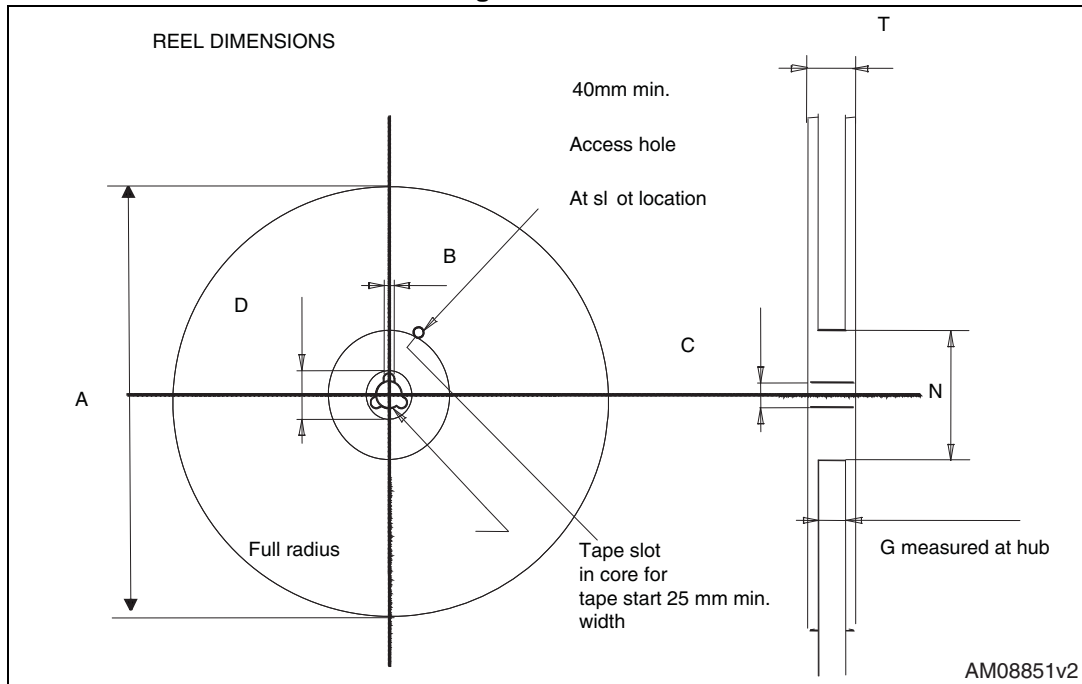


Table 13. H²PAK-2 tape and reel mechanical data

Tape			Reel		
Dim.	mm		Dim.	mm	
	Min.	Max.		Min.	Max.
A0	10.5	10.7	A		330
B0	15.7	15.9	B	1.5	
D	1.5	1.6	C	12.8	13.2
D1	1.59	1.61	D	20.2	
E	1.65	1.85	G	24.4	26.4
F	11.4	11.6	N	100	
K0	4.8	5.0	T		30.4
P0	3.9	4.1			
P1	11.9	12.1	Base qty		1000
P2	1.9	2.1	Bulk qty		1000
R	50				
T	0.25	0.35			
W	23.7	24.3			

6 Revision history

Table 14. Document revision history

Date	Revision	Changes
12-Jan-2007	1	First release
17-Apr-2007	2	Added new value on Table 6 .
14-May-2007	3	The document has been reformatted
29-Aug-2007	4	$R_{DS(on)}$ value changed, updated Figure 15
09-Apr-2008	5	Added new package: TO-3PF
13-Feb-2009	6	Added P_{TOT} value for TO-3PF (Table 2: Absolute maximum ratings)
01-Dec-2009	7	<ul style="list-style-type: none"> – Document status promoted from preliminary data to datasheet – Removed TO-220FH package and mechanical data
10-Dec-2009	8	Corrected V_{ISO} value in Table 2: Absolute maximum ratings
29-Jun-2010	9	Corrected unit in Table 3 .
08-Feb-2013	10	<ul style="list-style-type: none"> – Minor text changes – Modified: Table 3 – Changed: Figure 1 – Added: H²PAK-2 package
18-Feb-2014	11	<ul style="list-style-type: none"> – Modified: Figure 1 – Updated: Figure 18, 19, 20 and 21 – Updated: Figure 27 and Table 11 – Updated: Section 4: Package mechanical data – Minor text changes

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